## Jan Muszalski

## List of Publications by Citations

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21 218 9 14 g-index

29 284 2.1 2.46 ext. papers ext. citations avg, IF L-index

#	Paper	IF	Citations
21	Measurement of linewidth enhancement factor in self-assembled quantum dot semiconductor lasers emitting at 1310 nm. <i>Electronics Letters</i> , <b>2004</b> , 40, 428	1.1	34
20	The effect of pressure on the luminescence from GaAs/AlGaAs quantum wells. <i>Semiconductor Science and Technology</i> , <b>1994</b> , 9, 2239-2246	1.8	26
19	Static phase diagrams of reconstructions for MBE-grown GaAs(001) and AlAs(001) surfaces. <i>Thin Solid Films</i> , <b>1995</b> , 267, 54-57	2.2	22
18	MBE growth of strain-compensated InGaAs/InAlAs/InP quantum cascade lasers. <i>Journal of Crystal Growth</i> , <b>2017</b> , 466, 22-29	1.6	19
17	Molecular-beam epitaxy growth and characterization of mid-infrared quantum cascade laser structures. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 565-569	1.8	17
16	The influence of the growth rate and V/III ratio on the crystal quality of InGaAs/GaAs QW structures grown by MBE and MOCVD methods. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 4423-4432	1.6	17
15	The influence of the growth temperature and interruption time on the crystal quality of InGaAs/GaAs QW structures grown by MBE and MOCVD methods. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 2785-2792	1.6	17
14	Highly efficient heat extraction by double diamond heat-spreaders applied to a vertical external cavity surface-emitting laser. <i>Optical and Quantum Electronics</i> , <b>2017</b> , 49, 1	2.4	11
13	Photoluminescence mapping and angle-resolved photoluminescence of MBE-grown InGaAs/GaAs RC LED and VCSEL structures. <i>Thin Solid Films</i> , <b>2002</b> , 412, 114-121	2.2	9
12	Switchable double wavelength generating vertical external cavity surface-emitting laser. <i>Optics Express</i> , <b>2014</b> , 22, 6447-52	3.3	8
11	Pyrometric interferometry during MBE growth of laser heterostructures. <i>Thin Solid Films</i> , <b>2000</b> , 367, 299-301	2.2	8
10	Membrane external-cavity surface-emitting laser emitting at 1640 nm. Optics Letters, 2020, 45, 539	3	7
9	Dual-wavelength vertical external-cavity surface-emitting laser: strict growth control and scalable design. <i>Applied Physics B: Lasers and Optics</i> , <b>2016</b> , 122, 1	1.9	4
8	A 95-nm-wide Tunable Two-Mode Vertical External Cavity Surface-Emitting Laser. <i>IEEE Photonics Technology Letters</i> , <b>2017</b> , 29, 2215-2218	2.2	4
7	The effect of the MBE growth rate on the surface phase diagram for GaAs (001). <i>Thin Solid Films</i> , <b>1995</b> , 267, 51-53	2.2	4
6	Impact of strain on periodic gain structures in vertical external cavity surface-emitting lasers. <i>Applied Physics B: Lasers and Optics</i> , <b>2016</b> , 122, 1	1.9	3
5	High-Power 1770 nm Emission of a Membrane External-Cavity Surface-Emitting Laser. <i>IEEE Journal of Quantum Electronics</i> , <b>2021</b> , 57, 1-6	2	3

## LIST OF PUBLICATIONS

4	Nanoindentation of GaAs/AlAs distributed bragg reflector grown on GaAs substrate. <i>Materials Science in Semiconductor Processing</i> , <b>2020</b> , 109, 104912	4.3	1
3	Improvement of quantum efficiency of MBE grown AlGaAs/InGaAs/GaAs edge emitting lasers by optimisation of construction and technology. <i>Vacuum</i> , <b>2007</b> , 82, 383-388	3.7	1
2	Growth and characterization of InP-based 1750 nm emitting membrane external-cavity surface-emitting laser. <i>Applied Physics B: Lasers and Optics</i> , <b>2020</b> , 126, 1	1.9	1
1	Optical examination of high contrast grating fabricated by focused-ion beam etching. <i>Optical and Quantum Electronics</i> , <b>2016</b> , 48, 1	2.4	